

±35kV High-ESD Profibus RS-485 Transceiver

General Description

The MAX14770E is a half-duplex, ±35kV high ESDprotected, 20Mbps transceiver for PROFIBUS-DP and RS-485 applications. In addition, it can be used for RS-422/V.11 communications. The MAX14770E is designed to meet IEC 61158-2, TIA/EIA-422-B, TIA/EIA-485-A, V.11, and X.27 standards.

The MAX14770E is available in an 8-pin SO and an 8-pin µMAX® specified over the extended temperature range. It is also available in a tiny TDFN (3mm x 3mm) package and specified over the automotive (-40°C to +125°C) temperature range.

Applications

PROFIBUS-DP Networks Industrial Fieldbuses Motion Controllers **RS-485** Networks

Machine Encoders

data sheet.

Benefits and Features

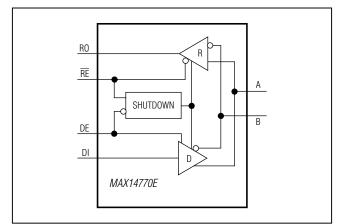
- Integrated Protection Increases Robustness ±35kV HBM ESD per JEDEC JS-001-2012 ±12kV Contact ESD per IEC 61000-4-2 ±15kV Air Gap ESD per IEC 61000-4-2 **True Fail-Safe Receiver Prevents False** Transitions on Receiver Input Short or Open Hot Swap Eliminates False Transitions During **Power-Up or Hot Insertion Short-Circuit-Protected Outputs Thermal Shutdown Circuitry Prevents Excessive Power Dissipation**
- Low Current Reduces Power Consumption 15µA Shutdown Current 2.5mA Supply Current Typical with No Load
- Profibus Compliant with Minimum 20Mbps Data Rate
- Allows Up to 128 Transceivers on the Bus
- ♦ -40°C to +125°C Automotive Temperature Range in Tiny 8-Pin (3mm x 3mm) TDFN

Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	TOP MARK
MAX14770EESA+T	-40°C to +85°C	8 SO	—
MAX14770EGSA+T	-40°C to +105°C	8 SO	—
MAX14770EGUA+T	-40°C to +105°C	8 µMAX	_
MAX14770EATA+T	-40°C to +125°C	8 TDFN-EP*	BMG

+Denotes a lead(Pb)-free/RoHS-compliant package. T = Tape and reel.

*EP = Exposed pad.



Typical PROFIBUS-DP Operating Circuit appears at end of

Functional Diagram

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For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642. or visit Maxim's website at www.maximintegrated.com.

ABSOLUTE MAXIMUM RATINGS

(Voltages referenced to GND.)

Vcc	0.3V to +6.0V
RE, RO0	.3V to (VCC + 0.3V)
DE, DI	0.3V to +6.0V
A, B	8.0V to +13.0V
Short-Circuit Duration (RO, A, B) to GND	Continuous
Continuous Power Dissipation ($T_A = +70^{\circ}C$))
SO (derate 7.6mW/°C above +70°C)	606mW
TDFN (derate 24.4mW/°C above +70°C).	1951mW
µMAX (derate 4.8mW/°C above +70°C)	387.8mW

Operating Temperature Range	
MAX14470EESA	40°C to +85°C
MAX14470EG_A	40°C to +105°C
MAX14470EATA	40°C to +125°C
Storage Temperature Range	65°C to +150°C
Junction Temperature Range	40°C to +150°C
Lead Temperature (soldering, 10s)	+300°C
Soldering Temperature (reflow)	+260°C

PACKAGE THERMAL CHARACTERISTICS (Note 1)

SO
Junction-to-Ambient Thermal Resistance (0JA)132°C/W
Junction-to-Case Thermal Resistance (0JC)
μΜΑΧ
Junction-to-Ambient Thermal Resistance (0JA)206.3°C/W
Junction-to-Case Thermal Resistance (0JC)42°C/W

TDFN

Junction-to-Ambient Thermal Resistance (θ_{JA})......41°C/W Junction-to-Case Thermal Resistance (θ_{JC})...........8°C/W

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

$(V_{CC} = +5V \pm 10\%, T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Ty	/pical values are at V _{CC} = +5V, T_A = +25°C.) (Note 2)
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PARAMETER	SYMBOL	CONDITIONS		ТҮР	MAX	UNITS	
Power-Supply Range	Vcc		4.5		5.5	V	
Supply Current	ICC	DE = 1, \overline{RE} = 0 or DE = 0, \overline{RE} = 0 or DE = 1, \overline{RE} = 1; no load		2.5	4	mA	
Shutdown Supply Current	ISH	DE = 0, RE = 1			15	μA	
DRIVER							
Differential Driver Output	IVODI	$R_L = 54\Omega$, DI = V _{CC} or GND; Figure 1	2.1			V	
Differential Driver Peak-to-Peak Output	VODPP	Figure 2 (Note 3)	4.0		6.8	V	
Change in Magnitude of Differential Output Voltage	ΔVod	$R_L = 54\Omega$; Figure 1 (Note 4)	-0.2	0	+0.2	V	
Driver Common- Mode Output Voltage	Voc	$R_L = 54\Omega$; Figure 1		1.8	3	V	
Change in Common- Mode Voltage	ΔVoc	$R_L = 54\Omega$; Figure 1 (Note 4)	-0.2		+0.2	V	
Driver Short-Circuit Output Current	IOSD	$0V \le V_{OUT} \le +12V$; output low			+250	mA	
(Note 5)		$-7V \le V_{OUT} \le V_{CC}$; output high	-250				

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +5V \pm 10\%, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } V_{CC} = +5V, T_A = +25^{\circ}C.)$ (Note 2)

PARAMETER	SYMBOL	CONDITION	S	MIN	TYP	MAX	UNITS
Driver Short-Circuit		$(V_{CC} - 1V) \le V_{OUT} \le +12V; outp$	out low	-15			
Foldback Output Current (Note 5)	IOSDF	$-7V \le V_{OUT} \le +1V$; output high				+15	mA
LOGIC INPUTS	1			1			
Driver Input High Voltage	VIH	DE, DI, RE		2.0			V
Driver Input Low Voltage	VIL	DE, DI, RE				0.8	V
Driver Input Hysteresis	VHYS	DE, DI, RE			50		mV
Driver Input Current	lin	DE, DI, RE		-1		+1	μA
Input Impedance in	R _{DE}	Figure 11 until the first low-to-hi occurs	gh transition of DE	- 1	5.6	10	kΩ
Hot Swap	RRE	Figure 11 until the first high-to-low transition of RE occurs					
RECEIVER				1			
Input Current (A, B)	IA, IB	$DE = GND, V_{CC} = V_{GND}$ or	V _{IN} = 12V			+250	μA
	, _	+5.5V	$V_{IN} = -7V$	-200	-		
Differential Input Capacitance	Сав	Between A and B, DE = \overline{RE} = GND at 6MHz			8		pF
Receiver Differential Threshold Voltage	VTH	$-7V \le V_{CM} \le 12V$		-200	-125	-50	mV
Receiver Input Hysteresis	ΔV _{TH}	V _{CM} = 0V			15		mV
LOGIC OUTPUT							
Output High Voltage	Voh	$I_{OUT} = -6mA, V_A - V_B = V_{TH}$		4			V
Output Low Voltage	Vol	IOUT = 6mA, VA - VB = -VTH				0.4	V
Three-State Receiver Output Current	Iozr	$0V \le V_{OUT} \le V_{CC}$		-1		+1	μA
Receiver Input Resistance	RIN	$-7V \le V_{CM} \le 12V$		48			kΩ
Receiver Output Short-Circuit Current	IOSR	$0V \le V_{RO} \le V_{CC}$		-110		+110	mA
PROTECTION SPECIF	ICATIONS						
Thermal-Shutdown Threshold	VTS				+160		°C
Thermal-Shutdown Hysteresis	VTSH				15		°C
		HBM			±35		
ESD Protection, A and B Pins		IEC 61000-4-2 Air-Gap Discharge to GND			±20	±20	
		IEC 61000-4-2 Contact Dischar	ge to GND		±10		

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +5V \pm 10\%, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } V_{CC} = +5V, T_A = +25^{\circ}C.)$ (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
ESD Protection, All Other Pins		НВМ		±2		kV
DRIVER SWITCHING	CHARACTERIS	STICS				
Driver Propagation Delay	tdplh tdphl	$R_L = 54\Omega$, $C_L = 50pF$; Figures 3 and 4		15	28	ns
Differential Driver Output Skew It _{DPLH} - t _{DPHL} I	^t DSKEW	R_L = 54 Ω,C_L = 50pF; Figures 3 and 4		1.2		ns
Driver Output Transition Skew Itt(MLH) ^I , Itt(MHL) ^I	t TSKEW	R_L = 54 Ω,C_L = 50pF; Figures 3 and 5		2		ns
Driver Differential Output Rise or Fall Time	tLH, tHL	R_L = 54 $\Omega,~C_L$ = 50pF; Figures 3 and 4		7	15	ns
Maximum Data Rate			20			Mbps
Driver Enable to Output High	tdzh	$R_L = 500\Omega$, $C_L = 50pF$; Figure 6		25	48	ns
Driver Enable to Output Low	tDZL	$R_L = 500\Omega$, $C_L = 50pF$; Figure 7		25	48	ns
Driver Disable Time from Low	tDLZ	$R_L = 500\Omega$, $C_L = 50pF$; Figure 7		20	40	ns
Driver Disable Time from High	tDHZ	$R_L = 500\Omega$, $C_L = 50pF$, Figure 6		20	40	ns
Driver Enable Skew Time	ltzL - tzHl	$R_L = 500\Omega$, $C_L = 50pF$; Figures 6 and 7			8	ns
Driver Disable Skew Time	lt_z - t _{HZ} I	$R_L = 500\Omega$, $C_L = 50pF$; Figures 6 and 7			8	ns
Driver Enable High— Propagation Delay Difference	tdzh - tdphl			8	20	ns
Driver Enable Low— Propagation Delay Difference	tdzl - tdphl			10	20	ns
Driver Enable from Shutdown to Output High	tDZL(SHDN)	$R_L = 500\Omega$, $C_L = 50pF$; Figure 7 (Note 6)		46	100	μs
Driver Enable from Shutdown to Output Low	tDZH(SHDN)	$R_L = 500\Omega$, $C_L = 50pF$; Figure 6 (Note 6)		46	100	μs
Time to Shutdown	tSHDN	(Note 6)	50		800	ns

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ELECTRICAL CHARACTERISTICS (continued)

(VCC = +5V ±10%, TA = TMIN to TMAX, unless otherwise noted. Typical values are at VCC = +5V, TA = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		ТҮР	MAX	UNITS	
RECEIVER SWITCHIN	RECEIVER SWITCHING CHARACTERISTICS						
Receiver Propagation	^t RPLH	$C_L = 15pF;$ Figures 8 and 9 (Note 7)			28	ns	
Delay	t RPHL				20	115	
Receiver Output Skew	t RSKEW	$C_L = 15pF$; Figures 8 and 9 (Notes 7, 8)			2	ns	
Maximum Data Rate			20			Mbps	
Receiver Enable to Output High	^t RZH	S2 closed; R _L = 1k Ω , C _L = 15pF; Figure 10			30	ns	
Receiver Enable to Output Low	trzl	S1 closed; $R_L = 1k\Omega$, $C_L = 15pF$; Figure 10			30	ns	
Receiver Disable Time from Low	^t RLZ	S1 closed; R _L = 1k Ω , C _L = 15pF; Figure 10			30	ns	
Receiver Disable Time from High	^t RHZ	S2 closed; R _L = 1k Ω , C _L = 15pF; Figure 10			30	ns	
Receiver Enable from Shutdown to Output High	trzl(SHDN)	S1 closed; R _L = 1k Ω , C _L = 15pF; Figure 10 (Notes 6, 7)			100	μs	
Receiver Enable from Shutdown to Output Low	^t RZH(SHDN)	S2 closed; RL = 1k Ω , CL = 15pF; Figure 10 (Notes 6, 7)			100	μs	
Time to Shutdown	tshdn	(Note 6)	50		800	ns	

Note 2: Devices are production tested at $T_A = +25^{\circ}C$. Specifications over temperature limits are guaranteed by design.

Note 3: VODPP is the difference in VOD, with the DI at high and DI at low.

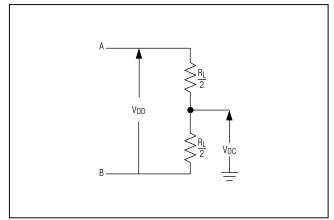
Note 4: ΔV_{OD} and ΔV_{OC} are the changes in IV_{OD}I and IV_{OC}I, respectively, with the DI at high and DI at low.

Note 5: The short-circuit output current applies to peak current just prior to foldback current limiting; the short-circuit foldback output current applies during current limiting to allow a recovery from bus contention.

Note 6: Shutdown is enabled by bringing RE high and DE low. If the enable inputs are in this state for less than 50ns, the device is guaranteed not to enter shutdown. If the enable inputs are in this state for at least 800ns, the device is guaranteed to have entered shutdown.

Note 7: Capacitive load includes test probe and fixture capacitance.

Note 8: Guaranteed by characterization; not production tested.



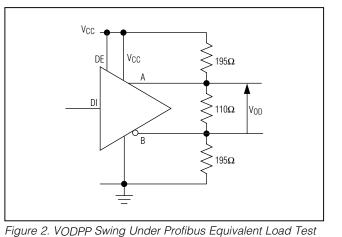


Figure 1. Driver DC Test Load

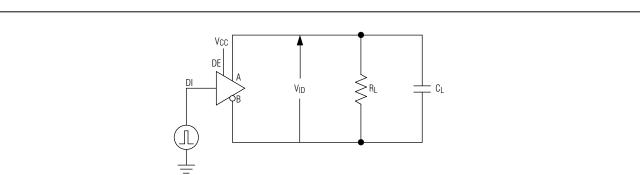


Figure 3. Driver Timing Test Circuit

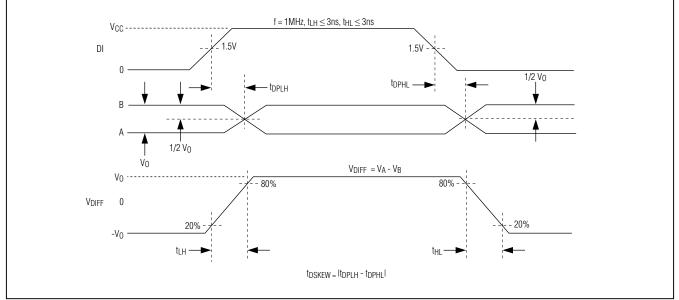


Figure 4. Driver Propagation Delays

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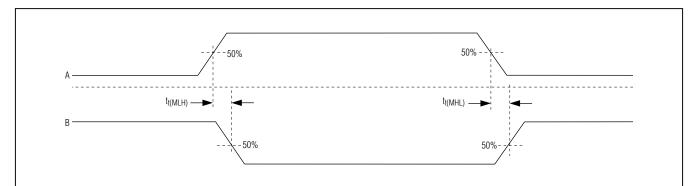


Figure 5. Driver Transition Skew

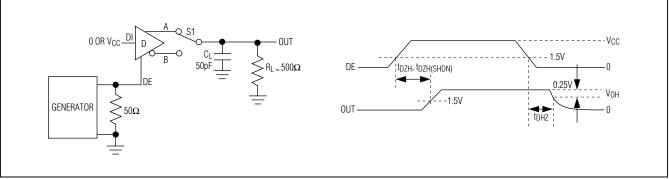


Figure 6. Driver Enable and Disable Times

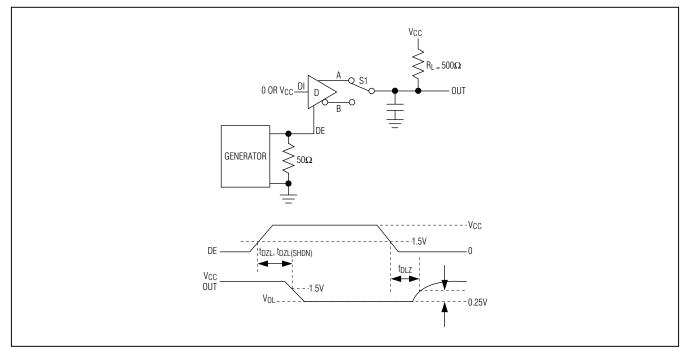


Figure 7. Driver Enable and Disable Times

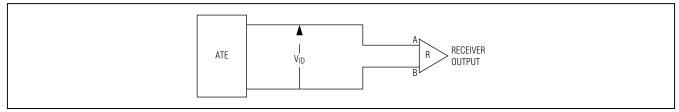


Figure 8. Receiver Propagation Delay Test Circuit

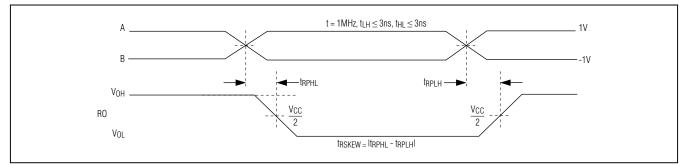


Figure 9. Receiver Propagation Delays

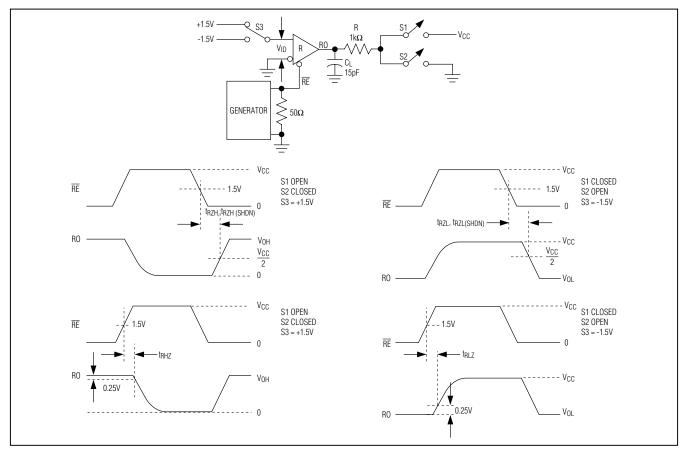
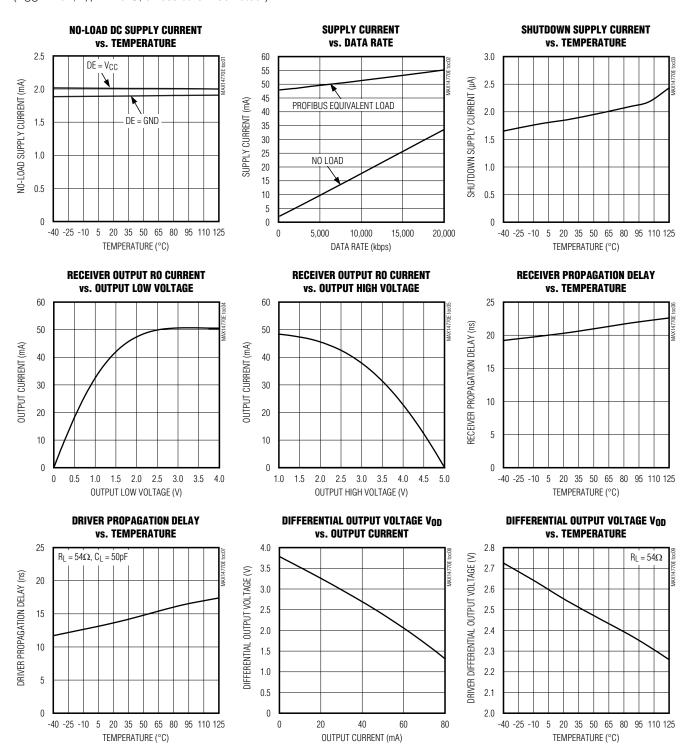


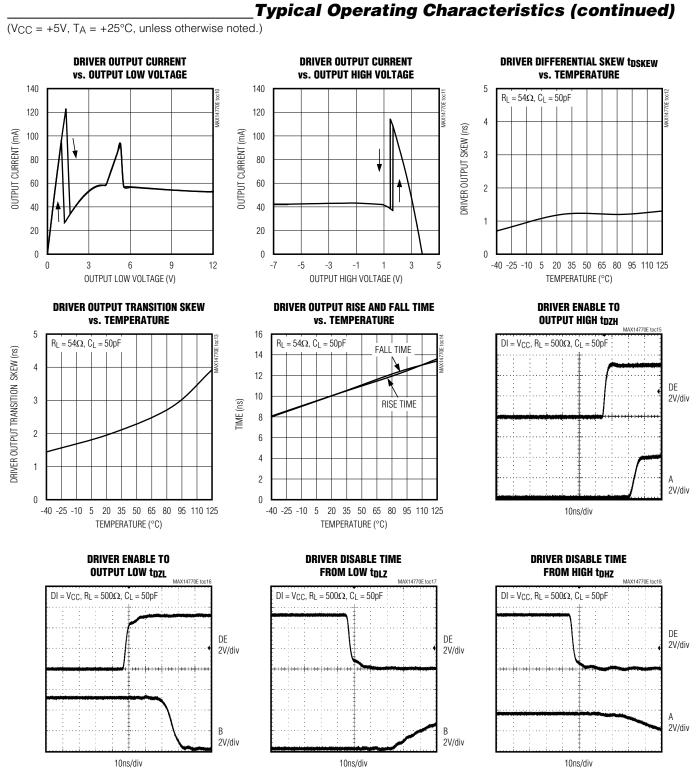
Figure 10. Receiver Enable and Disable Times

Typical Operating Characteristics

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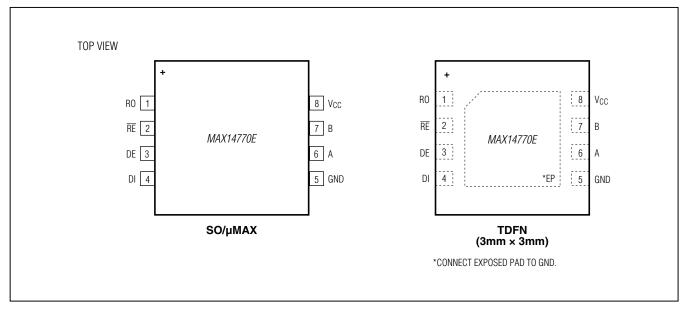
$(V_{CC} = +5V, T_A = +25^{\circ}C, unless otherwise noted.)$



Maxim Integrated

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Pin Configurations



Pin Description

PIN	NAME	FUNCTION
1	RO	Receiver Output. When \overline{RE} is low and (A - B) \geq -50mV, RO is high; if (A - B) \leq -200mV, RO is low.
2	RE	Receiver Enable. Drive \overline{RE} low to enable RO; RO is high impedance when \overline{RE} is high. Drive \overline{RE} high and DE low to enter low-power shutdown mode.
3	DE	Driver Enable. Drive DE high to enable driver output. The driver outputs are high impedance when DE is low. Drive $\overline{\text{RE}}$ high and DE low to enter low-power shutdown mode.
4	DI	Driver Input. With DE high, a low on DI forces the noninverting output, A, low and the inverting output, B, high. Similarly, a high on DI forces the noninverting output, A, high and the inverting output, B, low.
5	GND	Ground
6	A	Noninverting Receiver Input and Noninverting Driver Output
7	В	Inverting Receiver Input and Inverting Driver Output
8	8 VCC Positive Supply. Bypass V _{CC} to GND with a 0.1μF ceramic capacitor as close as possible to th device.	
	EP	Exposed Pad (TDFN Only). Connect EP to GND.

Detailed Description

The MAX14770E is a half-duplex, ± 35 kV high ESDprotected transceiver for PROFIBUS-DP, RS-485, and RS-422 communications. The device features true failsafe circuitry that guarantees a logic-high receiver output when the receiver inputs are open or shorted, or when they are connected to a terminated transmission line with all drivers disabled (see the *True Fail-Safe* section). The MAX14770E supports data rates up to 20Mbps.

The MAX14770E operates from a single +4.5V to +5.5V supply. Drivers are output short-circuit current limited. Thermal-shutdown circuitry protects drivers against excessive power dissipation. When activated, the thermal-shutdown circuitry places the driver outputs into a high-impedance state. The MAX14770E has a hot-swap input structure that prevents disturbances on the differential signal lines when the MAX14770E is powered up (see the *Hot-Swap Capability* section).

True Fail-Safe

The MAX14770E guarantees a logic-high receiver output when the receiver inputs are shorted or open, or when they are connected to a terminated transmission line with all drivers disabled. This is done by having the receiver

Table 1. Functional Table (Transmitting)

TRANSMITTING					
	INPUTS			PUTS	
RE	DE	DI	В	Α	
Х	1	1	0	1	
Х	1	0	1	0	
0	0	Х	High-Z	High-Z	
1	0	Х	X High-Z and shutdown		

X = Don't care.

Table 2. Functional Table (Receiving)

	RECEIVING				
	INPU	OUTPUT			
RE	DE A-B		RO		
0	Х	≥ -0.05V	1		
0	Х	≤ -0.2V	0		
0	Х	Open/shorted	1		
1	1	Х	High-Z		
1	0	Х	High-Z and shutdown		

X = Don't care.

threshold between -50mV and -200mV. If the differential receiver input voltage (A - B) is greater than or equal to -50mV, RO is logic-high. If (A - B) is less than or equal to -200mV, RO is logic-low. In the case of a terminated bus with all transmitters disabled, the receiver's differential input voltage is pulled to 0V by the termination. With the receiver thresholds of the MAX14770E, this results in a logic-high with a 50mV minimum noise margin. The -50mV to -200mV threshold complies with the ±200mV EIA/TIA-485 standard.

Hot-Swap Capability

Hot-Swap Inputs

When circuit boards are inserted into a hot or powered backplane, disturbances to the enable inputs and differential receiver inputs can lead to data errors. Upon initial circuit board insertion, the processor undergoes its power-up sequence. During this period, the processor output drivers are high impedance and are unable to drive the DE and $\overline{\text{RE}}$ inputs of the MAX14770E to a defined logic level. Leakage currents up to 10µA from the high-impedance output of a controller could cause DE and $\overline{\text{RE}}$ to drift to an incorrect logic state. Additionally, parasitic circuit board capacitance could cause coupling of VCC or GND to DE and $\overline{\text{RE}}$. These factors could improperly enable the driver or receiver. However, the MAX14770E has hot-swap inputs that avoid these potential problems.

When V_{CC} rises, an internal pulldown circuit holds DE low and \overline{RE} high. After the initial power-up sequence, the pulldown circuit becomes transparent, resetting the hot-swap-tolerable inputs.

Hot-Swap Input Circuitry

The MAX14770E DE and RE enable inputs feature hot-swap capability. At the input, there are two NMOS devices, M1 and M2 (Figure 11). When VCC ramps from 0, an internal 15µs timer turns on M2 and sets the SR latch that also turns on M1. Transistors M2, a 1mA current sink, and M1, a 100µA current sink, pull DE to GND through a 5.6k Ω resistor. M2 is designed to pull DE to the disabled state against an external parasitic capacitance up to 100pF that can drive DE high. After 15µs, the timer deactivates M2 while M1 remains on, holding DE low against three-state leakages that can drive DE high. M1 remains on until an external source overcomes the required input current. At this time, the SR latch resets and M1 turns off. When M1 turns off, DE reverts to a standard, high-impedance CMOS input. Whenever VCC drops below 1V, the hot-swap input is reset.

For RE, there is a complementary circuit employing two PMOS devices pulling RE to V_{CC}.

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Thermal-Shutdown Protection

The MAX14770E features thermal-shutdown circuitry. The internal switch turns off when the junction temperature exceeds $+160^{\circ}$ C (typ) and immediately goes into a fault mode. The device exits thermal shutdown after the junction temperature cools by 15°C (typ).

Applications Information

128 Transceivers on the Bus

The standard RS-485 receiver input impedance is one unit load, and a standard driver can drive up to 32 unit loads. The MAX14770E transceiver has a 1/4 unit load receiver, which allows up to 128 transceivers connected in parallel on one communication line. Connect any combination of these devices, and/or other RS-485 devices, for a maximum of 32 unit loads to the line.

Low-Power Shutdown Mode

Low-power shutdown mode is initiated by bringing both $\overline{\text{RE}}$ high and DE low. In shutdown, the devices draw only 15µA (max) of supply current. $\overline{\text{RE}}$ and DE can be driven simultaneously; the devices are guaranteed not to enter shutdown if $\overline{\text{RE}}$ is high and DE is low for less than 50ns. If the inputs are in this state for at least 800ns, the devices are guaranteed to enter shutdown.

Driver Output Protection

Two mechanisms prevent excessive output current and power dissipation caused by faults or by bus contention. The first, a foldback current limit on the output stage, provides immediate protection against short circuits over the whole common-mode voltage range (see the *Typical Operating Characteristics*). The second, a thermal-shutdown circuit, forces the driver outputs into a high-impedance state if the die temperature exceeds +160°C (typ).

Typical Application

The MAX14770E transceivers are designed for bidirectional data communications on multipoint bus transmission lines. Figure 12 shows a typical network applications circuit. To minimize reflections, the line should be terminated at both ends in its characteristic impedance, and stub lengths off the main line should be kept as short as possible.

Profibus Termination

The MAX14770E is designed for driving PROFIBUS-DP termination networks. With a worst-case loading of two termination networks with 220 Ω termination impedance and 390 Ω pullups/pulldowns, the drivers can drive V(A - B) > 2.1V output.

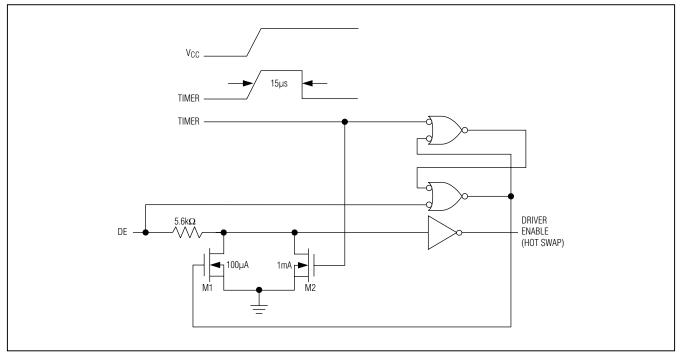


Figure 11. Simplified Structure of the Driver Enable Pin (DE)

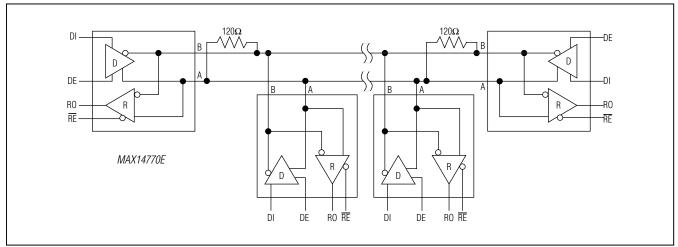


Figure 12. Typical Half-Duplex RS-485 Network

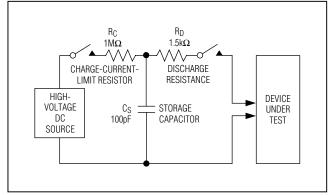


Figure 13. Human Body ESD Test Model

Extended ESD Protection

ESD protection structures are incorporated on all pins to protect against electrostatic discharges up to ± 2 kV (HBM) encountered during handling and assembly. A and B are further protected against high ESD up to ± 35 kV (HBM) without damage. The A and B pins are also protected against ± 20 kV Air-Gap and ± 10 kV Contact IEC61000-4-2 ESD events. The ESD structures withstand high ESD both in normal operation and when the device is powered down. After an ESD event, the MAX14770E continues to function without latchup.

ESD Test Conditions

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

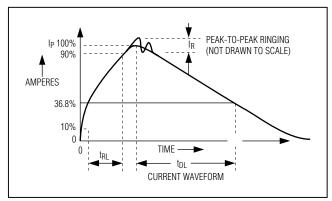


Figure 14. Human Body Current Waveform

Human Body Model

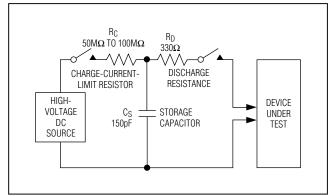
Figure 13 shows the HBM. Figure 14 shows the current waveform it generates when discharged into a low-impedance state. This model consists of a 100pF capacitor charged to the ESD voltage of interest that is then discharged into the device through a 1.5k Ω resistor.

IEC 61000-4-2

The IEC 61000-4-2 standard covers ESD testing and performance of finished equipment. It does not specifically refer to integrated circuits. The MAX14770E is specified for ± 20 kV Air-Gap Discharge and ± 10 kV Contact Discharge IEC 61000-4-2 on the A and B pins.

The main difference between tests done using the HBM and IEC 61000-4-2 is higher peak current in IEC 61000-4-2. Because series resistance is lower in the IEC 61000-4-2

±35kV High-ESD Profibus RS-485 Transceiver



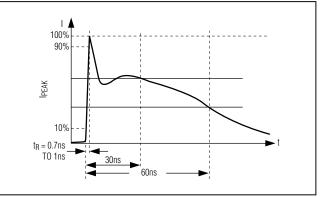
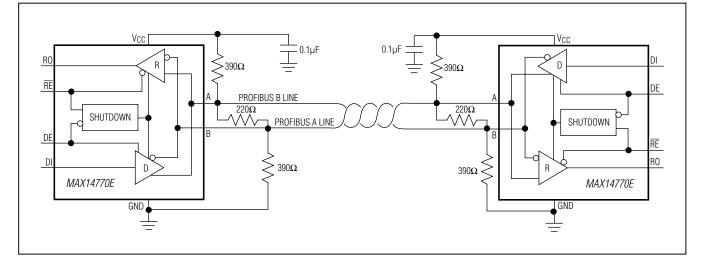


Figure 15. IEC61000-4-2 ESD Test Model

Figure 16. IEC61000-4-2 ESD Generator Current Waveform

Typical PROFIBUS-DP Operating Circuit



ESD test model (Figure 15), the ESD-withstand voltage measured to this standard is generally lower than that measured using the HBM. Figure 16 shows the current waveform for the \pm 10kV IEC 61000-4-2 Level 4 ESD Contact Discharge test. The Air-Gap Discharge test involves approaching the device with a charged probe. The Contact Discharge method connects the probe to the device before the probe is energized.

Chip Information

PROCESS: BiCMOS

Package Information

For the latest package outline information and land patterns, go to <u>www.maximintegrated.com/packages</u>. Note that a "+," "#," or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
8 SO	S8+4	<u>21-0041</u>	<u>90-0096</u>
8 TDFN-EP	T833+2	<u>21-0137</u>	<u>90-0059</u>
8 µMAX	U8+1	<u>21-0036</u>	<u>90-0092</u>

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	10/09	Initial release	_
1	4/10	Switched the position of the pins DE and DI (TDFN) in the Pin Configurations	11
2	1/11	Updated logic output specifications, TOC 15, and the <i>Typical PROFIBUS-DP</i> <i>Operating Circuit</i> , added the "Driver Enable High/Low—Propagation Delay Difference" parameters and updated various typical values in the <i>Electrical</i> <i>Characteristics</i> table	3, 4, 10, 15
3	10/12	Added µMAX and new SO packaging to data sheet	1, 2, 11, 15
4	2/13	Added missing 85°C SO information to data sheet	1, 2
5	1/15	Updated document title and <i>General Description</i> and <i>Benefits and Features</i> sections	1-16



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